

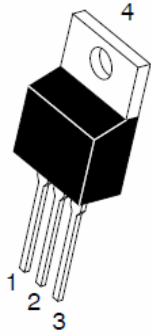


TSR30V60CT TSR30V60CTF

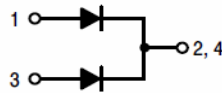
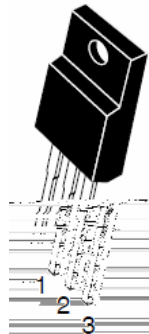
19-NOV-2013

Trench MOS Barrier Schottky Rectifier

TSR30V60CT
HC!



TSR30V60CTF
HC!



Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

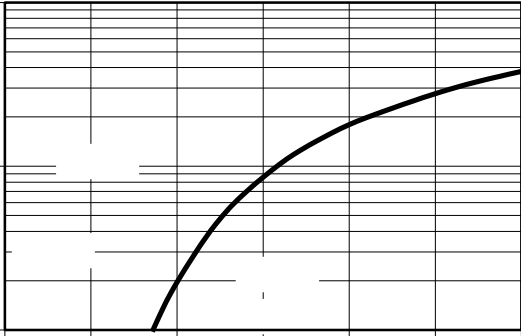
Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Limit		Unit
Maximum repetitive peak reverse voltage		V _{RRM}	60		V
Maximum average forward rectified current	per device	I _{F(AV)}	30		A
	per diode		15		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I _{FSM}	280		A
Operating junction and storage temperature range		T _J , T _{STG}	-40 to +150		°C
Typical thermal resistance per leg	TO-220	R _{JC}	2		°C/W
	TO-220Ø		4		°C/W
Instantaneous forward voltage per diode	I _F =5A	T _J =25°C	TYP.	MAX.	V
			0.38	-	
	I _F =15A	T _J =125°C	-	0.56	
			0.34	-	
Instantaneous reverse current per diode at rated reverse voltage		I _{R(2)}	-	50	µA
			30	-	mA

Notes:

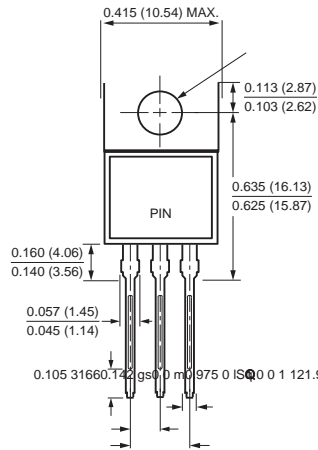
- (1) Pulse test: 300 µs pulse width, 1 % duty cycle
 (2) Pulse test: Pulse width ≤ 40 ms

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



PACKAGE OUTLINE DIMENSIONS

TO-220AB



TO-220F

